

### **FKI06190 Information**



For Reference Only

Part Number FKI06190 Manufacturer Sanken

Category Discrete Semiconductor Products

Transistors - FETs, MOSFETs - Single

**Description** MOSFET N-CH 60V 30A TO-220F

Package TO-220-3 Full Pack

For the pricing/inventory/lead time, please contact

us

Website: https://www.heisener.com E-mail: salesdept@heisener.com



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# **FKI06190 Specifications**

Manufacturer Part Number  Manufacturer  Sanken  Category  Discrete Semiconductor Products  Transistors - FETs, MOSFETs - Single  Package  TO-220-3 Full Pack  Series  - FET Type  N-Channel  Technology  MOSFET (Metal Oxide)  Drain to Source Voltage (Vdss)  Current - Continuous Drain (Id) @ 25°C  Drive Voltage (Max Rds On, Min Rds On)  Vgs(th) (Max) @ Id  Gate Charge (Qg) (Max) @ Vgs  Input Capacitance (Ciss) (Max) @ Vds  Vgs (Max)  FET Feature  Proceedings of the semiconductor Products  Analogous Sanken  Discrete Semiconductor Products  Transistors - FETs, MOSFETs - Single  TO-220-3 Full Pack  - Solve (Text)  Sanken  104  105  105  107  107  108  109  109  109  109  109  109  109		
Category  Discrete Semiconductor Products Transistors - FETs, MOSFETs - Single  Package  TO-220-3 Full Pack  Series  - FET Type  N-Channel  Technology  MOSFET (Metal Oxide)  Drain to Source Voltage (Vdss)  Current - Continuous Drain (Id) @ 25°C  Drive Voltage (Max Rds On, Min Rds On)  Vgs(th) (Max) @ Id  Gate Charge (Qg) (Max) @ Vgs  Input Capacitance (Ciss) (Max) @ Vds  Vgs (Max)  FET Feature  Discrete Semiconductor Products  Transistors - FETs, MOSFETs - Single  TO-220-3 Full Pack  -  30A (Tc)  30A (Tc)  25V @ 350µA  23.7nC @ 10V  1510pF @ 25V  420V  FET Feature	Manufacturer Part Number	FKI06190
Package         TO-220-3 Full Pack           Series         -           FET Type         N-Channel           Technology         MOSFET (Metal Oxide)           Drain to Source Voltage (Vdss)         60V           Current - Continuous Drain (Id) @ 25°C         30A (Tc)           Drive Voltage (Max Rds On, Min Rds On)         4.5V, 10V           Vgs(th) (Max) @ Id         2.5V @ 350μA           Gate Charge (Qg) (Max) @ Vgs         23.7nC @ 10V           Input Capacitance (Ciss) (Max) @ Vds         1510pF @ 25V           Vgs (Max)         ±20V           FET Feature         -	Manufacturer	Sanken
PackageTO-220-3 Full PackSeries-FET TypeN-ChannelTechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)60VCurrent - Continuous Drain (Id) @ 25°C30A (Tc)Drive Voltage (Max Rds On, Min Rds On)4.5V, 10VVgs(th) (Max) @ Id2.5V @ 350μAGate Charge (Qg) (Max) @ Vgs23.7nC @ 10VInput Capacitance (Ciss) (Max) @ Vds1510pF @ 25VVgs (Max)±20VFET Feature-	Category	Discrete Semiconductor Products
Series         -           FET Type         N-Channel           Technology         MOSFET (Metal Oxide)           Drain to Source Voltage (Vdss)         60V           Current - Continuous Drain (Id) @ 25°C         30A (Tc)           Drive Voltage (Max Rds On, Min Rds On)         4.5V, 10V           Vgs(th) (Max) @ Id         2.5V @ 350μA           Gate Charge (Qg) (Max) @ Vgs         23.7nC @ 10V           Input Capacitance (Ciss) (Max) @ Vds         1510pF @ 25V           Vgs (Max)         ±20V           FET Feature         -		Transistors - FETs, MOSFETs - Single
FET Type         N-Channel           Technology         MOSFET (Metal Oxide)           Drain to Source Voltage (Vdss)         60V           Current - Continuous Drain (Id) @ 25°C         30A (Tc)           Drive Voltage (Max Rds On, Min Rds On)         4.5V, 10V           Vgs(th) (Max) @ Id         2.5V @ 350μA           Gate Charge (Qg) (Max) @ Vgs         23.7nC @ 10V           Input Capacitance (Ciss) (Max) @ Vds         1510pF @ 25V           Vgs (Max)         ±20V           FET Feature         -	Package	TO-220-3 Full Pack
Technology  Drain to Source Voltage (Vdss)  Current - Continuous Drain (Id) @ 25°C  Drive Voltage (Max Rds On, Min Rds On)  Vgs(th) (Max) @ Id  Gate Charge (Qg) (Max) @ Vgs  Input Capacitance (Ciss) (Max) @ Vds  Vgs (Max)  FET Feature  MOSFET (Metal Oxide)  60V  30A (Tc)  30A (Tc)  2.5V @ 350μA  2.5V @ 350μA  1510pF @ 25V  4.5V, 10V  4.5V, 10V	Series	-
Drain to Source Voltage (Vdss)       60V         Current - Continuous Drain (Id) @ 25°C       30A (Tc)         Drive Voltage (Max Rds On, Min Rds On)       4.5V, 10V         Vgs(th) (Max) @ Id       2.5V @ 350μA         Gate Charge (Qg) (Max) @ Vgs       23.7nC @ 10V         Input Capacitance (Ciss) (Max) @ Vds       1510pF @ 25V         Vgs (Max)       ±20V         FET Feature       -	FET Type	N-Channel
Current - Continuous Drain (Id) @ 25°C       30A (Tc)         Drive Voltage (Max Rds On, Min Rds On)       4.5V, 10V         Vgs(th) (Max) @ Id       2.5V @ 350μA         Gate Charge (Qg) (Max) @ Vgs       23.7nC @ 10V         Input Capacitance (Ciss) (Max) @ Vds       1510pF @ 25V         Vgs (Max)       ±20V         FET Feature       -	Technology	MOSFET (Metal Oxide)
Drive Voltage (Max Rds On, Min Rds On)       4.5V, 10V         Vgs(th) (Max) @ Id       2.5V @ 350μA         Gate Charge (Qg) (Max) @ Vgs       23.7nC @ 10V         Input Capacitance (Ciss) (Max) @ Vds       1510pF @ 25V         Vgs (Max)       ±20V         FET Feature       -	Drain to Source Voltage (Vdss)	60V
Vgs(th) (Max) @ Id       2.5V @ 350μA         Gate Charge (Qg) (Max) @ Vgs       23.7nC @ 10V         Input Capacitance (Ciss) (Max) @ Vds       1510pF @ 25V         Vgs (Max)       ±20V         FET Feature       -	Current - Continuous Drain (Id) @ 25°C	30A (Tc)
Gate Charge (Qg) (Max) @ Vgs       23.7nC @ 10V         Input Capacitance (Ciss) (Max) @ Vds       1510pF @ 25V         Vgs (Max)       ±20V         FET Feature       -	Drive Voltage (Max Rds On, Min Rds On)	4.5V, 10V
Input Capacitance (Ciss) (Max) @ Vds	Vgs(th) (Max) @ Id	2.5V @ 350μA
Vgs (Max) ±20V FET Feature -	Gate Charge (Qg) (Max) @ Vgs	23.7nC @ 10V
FET Feature -	Input Capacitance (Ciss) (Max) @ Vds	1510pF @ 25V
	Vgs (Max)	±20V
D D' ' (' (M )	FET Feature	-
Power Dissipation (Max) 32W (1c)	Power Dissipation (Max)	32W (Tc)
Rds On (Max) @ Id, Vgs 15.3 mOhm @ 19.8A, 10V	Rds On (Max) @ Id, Vgs	15.3 mOhm @ 19.8A, 10V
Operating Temperature 150°C (TJ)	Operating Temperature	150°C (TJ)
Mounting Type Through Hole	Mounting Type	Through Hole
Supplier Device Package TO-220F	Supplier Device Package	TO-220F
Package / Case TO-220-3 Full Pack	Package / Case	TO-220-3 Full Pack
Report errors?		Report errors?

### **FKI06190 Guarantees**



#### **Quality Guarantees**

We provide 90 days warranty. \*

If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.



#### **Service Guarantees**

We guarantee 100% customer satisfaction.

Our experienced sales team and tech support team back our services to satisfy all our customers.

## **FKI06190 Payment Methods**





















### **FKI06190 Shipping Methods**













If you have any question about FKI06190, please do not hesitate to contact us!

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